

TOSHIBA Photocoupler GaAs Ired & Photo-Transistor

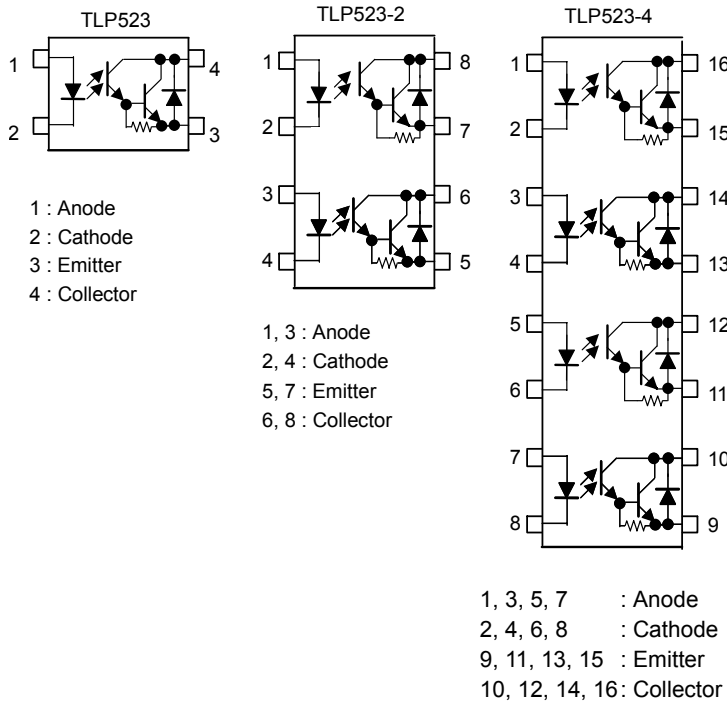
TLP523, TLP523-2, TLP523-4

Programmable Controllers
DC-Output Module
Solid State Relay

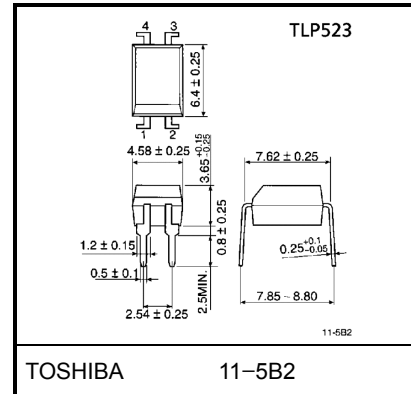
The TOSHIBA TLP523, -2 and -4 consists of a gallium arsenide infrared emitting diode coupled with a silicon, darlington connected, phototransistor which has an integral base-emitter resistor to optimize switching speed and elevated temperature characteristics. The TLP523-2 offers two isolated channels in a eight lead plastic DIP package, while the TLP523-4 provide four isolated channels per package.

- Current transfer ratio: 500% (min.) ($I_F = 1 \text{ mA}$)
- Isolation voltage: 2500 V_{rms} (min.)
- Collector-emitter voltage: 55 V (min.)
- Leakage current: 10 μA (max.) ($T_a = 85^\circ\text{C}$)
- UL recognized: UL1577, file no. E67349

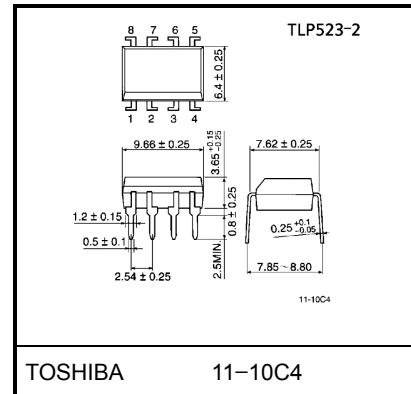
Pin Configurations (top view)



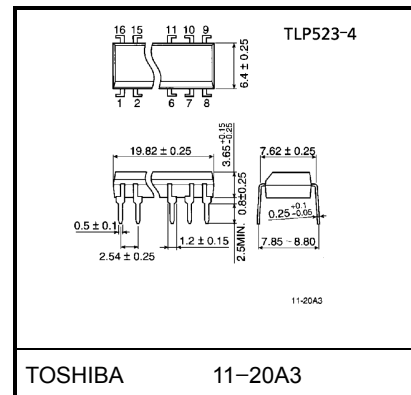
Unit in mm



Weight: 0.26 g



Weight: 0.54 g



Weight: 1.1 g

Maximum Ratings (Ta = 25°C)

Characteristic		Symbol	Rating		Unit
			TLP523	TLP523-2 TLP523-4	
LED	Forward current	I_F	60	50	mA
	Forward current derating	$\Delta I_F / ^\circ\text{C}$	-0.7 (Ta \geq 39°C)	-0.5 (Ta \geq 25°C)	mA / °C
	Pulse forward current	I_{FP}	1 (100µs pulse, 100pps)		A
	Reverse voltage	V_R	5		V
Detector	Collector-emitter voltage	V_{CEO}	55		V
	Emitter-collector voltage	V_{ECO}	0.3		V
	Collector current	I_C	150		mA
	Collector power dissipation (1 circuit)	P_C	150	100	mW
	Collector power dissipation derating (1 circuit (Ta \geq 25°C))	$\Delta P_C / ^\circ\text{C}$	-1.5	-1.0	mW / °C
	Operating temperature range	T_{opr}	-55~100		°C
Storage temperature range	T_{stg}	-55~125		°C	
Lead soldering temperature (10 s)	T_{sol}	260		°C	
Total power dissipation	P_T	250	150	mW	
Total power dissipation derating (Ta \geq 25°C)	$\Delta P_T / ^\circ\text{C}$	-2.5	-1.5	mW / °C	
Isolation voltage (Note 1)	BV_S	2500 (AC, 1min., R.H. \leq 60%)		Vrms	

(Note 1) Device considered a two terminal device: LED side pins shorted together and detector side pins shorted together.

Recommended Operating Conditions

Characteristic	Symbol	Min.	Typ.	Max.	Unit
Supply voltage	V_{CC}	—	5	24	V
Forward current	I_F	—	16	20	mA
Operating temperature range	T_{opr}	-25	—	85	°C

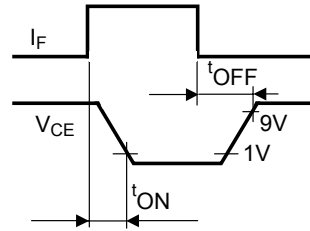
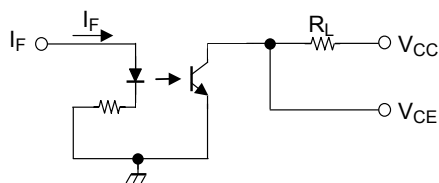
Electrical Characteristics (Ta = 25°C)

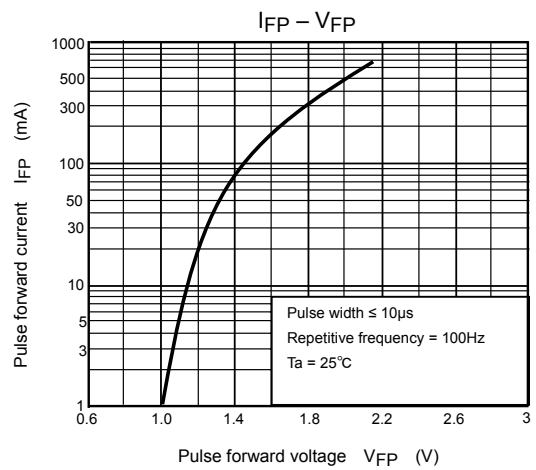
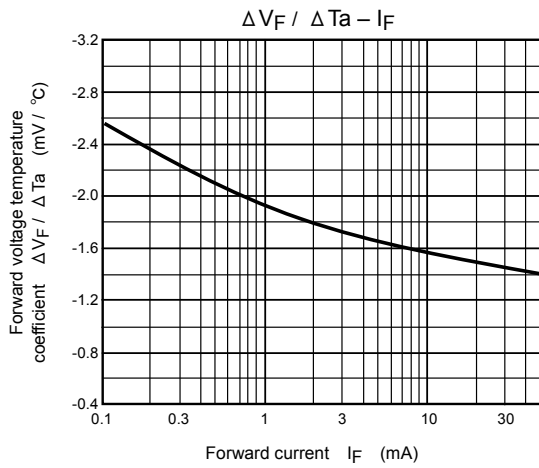
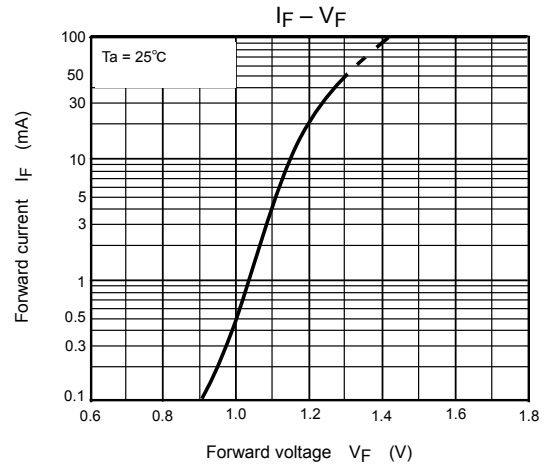
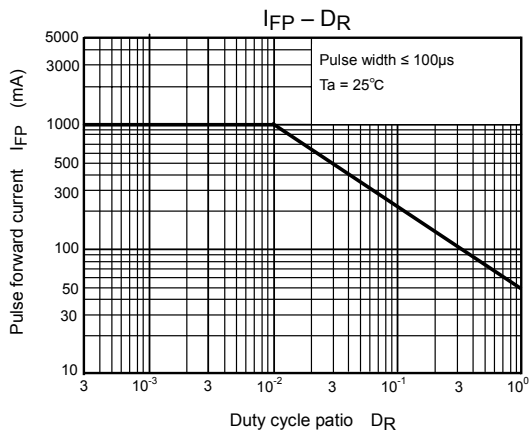
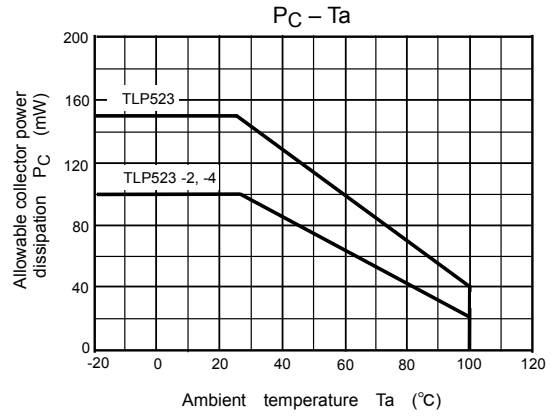
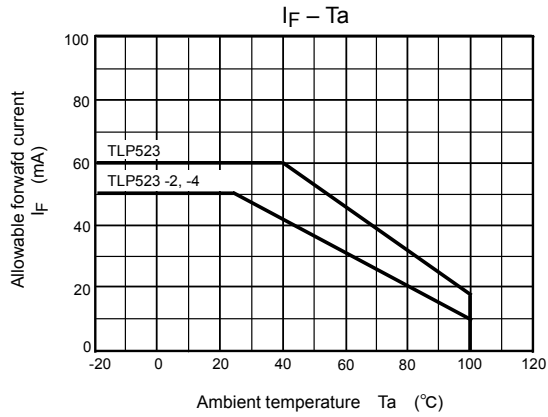
Characteristic		Symbol	Test Condition	Min.	Typ.	Max.	Unit
LED	Forward voltage	V_F	$I_F = 10 \text{ mA}$	1.0	1.15	1.3	V
	Reverse current	I_R	$V_R = 5 \text{ V}$	—	—	10	μA
	Capacitance	C_T	$V = 0, f = 1 \text{ MHz}$	—	30	—	pF
Detector	Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = 1 \text{ mA}$	55	—	—	V
	Collector dark current	I_{CEO}	$V_{CE} = 24 \text{ V}$	—	10	200	nA
			$V_{CE} = 24 \text{ V}, T_a = 85^\circ\text{C}$	—	0.5	10	μA
Capacitance collector to emitter	C_{CE}	$V = 0, f = 1 \text{ MHz}$	—	10	—	pF	
Coupled	Current transfer ratio	I_C / I_F	$I_F = 1 \text{ mA}, V_{CE} = 1 \text{ V}$	500	2000	—	%
	Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 50 \text{ mA}, I_F = 10 \text{ mA}$	—	—	1	V
	Capacitance input to output	C_S	$V_S = 0, f = 1 \text{ MHz}$	—	0.8	—	pF
	Isolation resistance	R_S	$V_S = 500 \text{ V}, R.H. \leq 60\%$	5×10^{10}	10^{14}	—	Ω

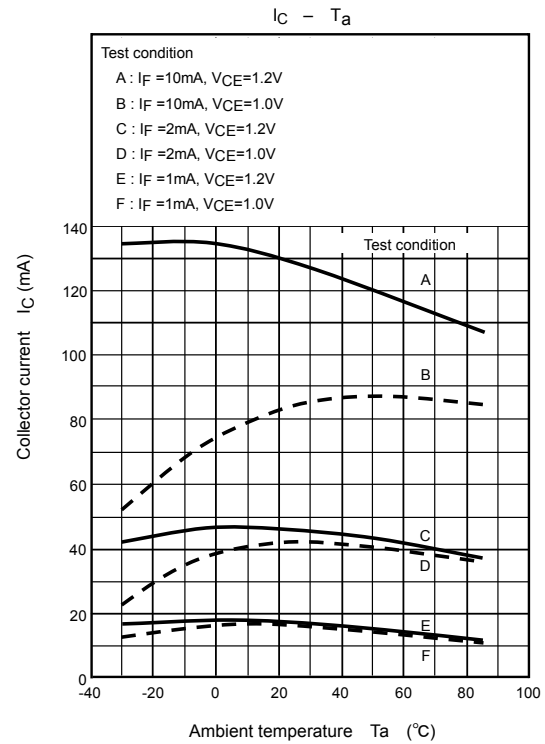
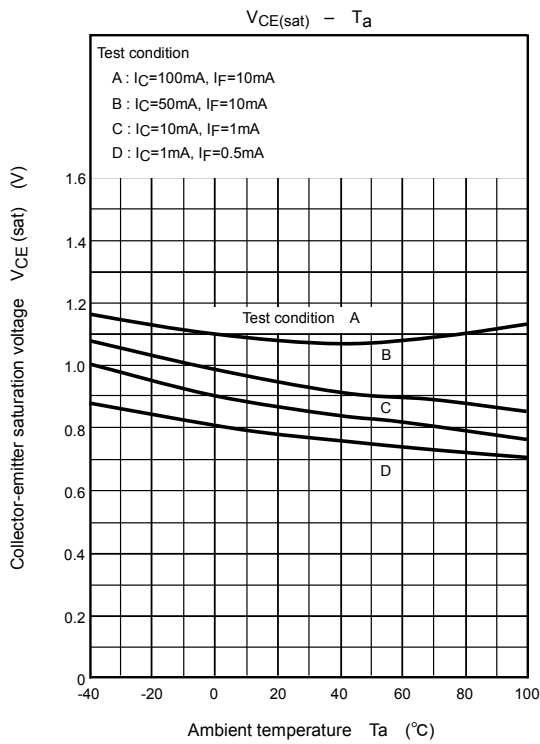
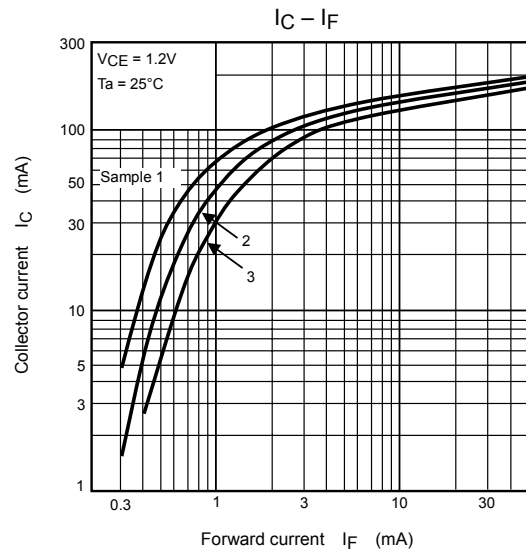
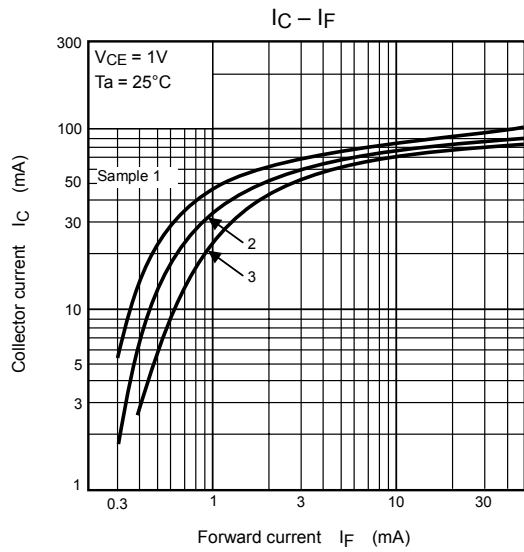
Switching Characteristics (Ta = 25°C)

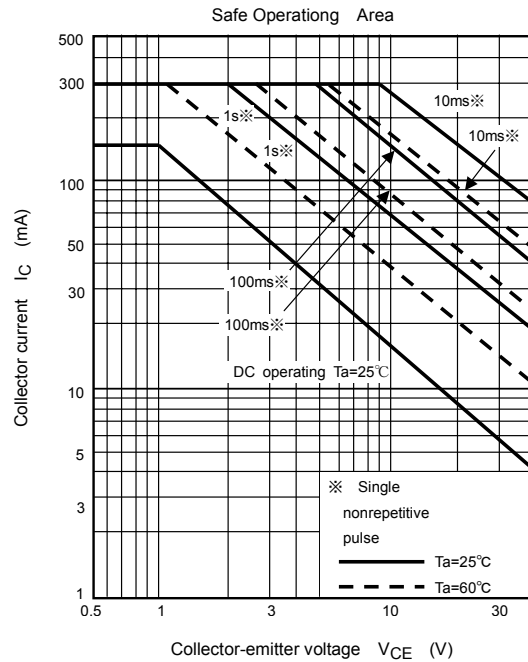
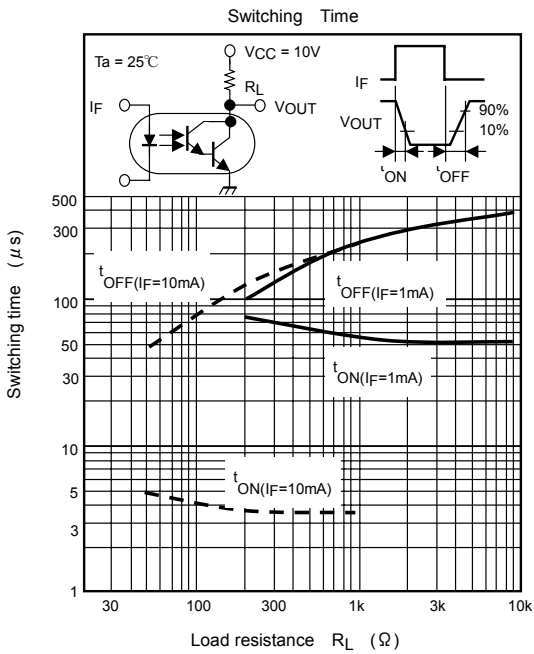
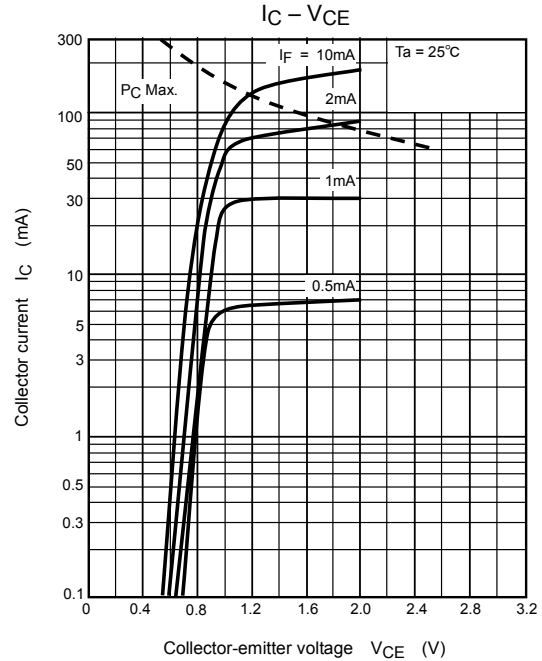
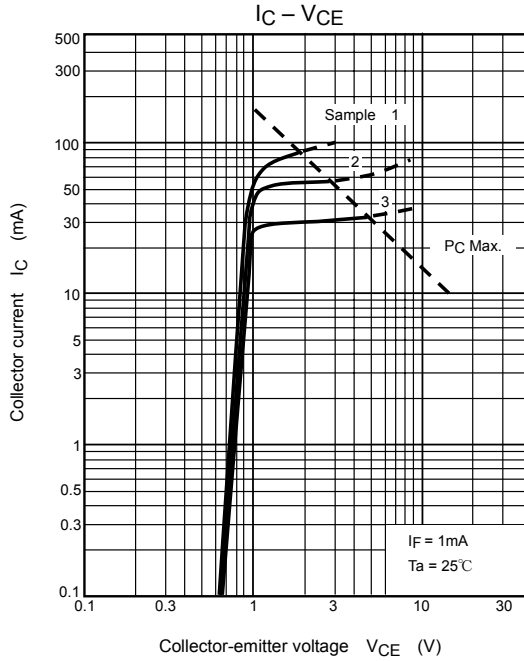
Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Turn-on time	t_{ON}	$V_{CC} = 10 \text{ V}, R_L = 180 \Omega$ $I_F = 16 \text{ mA}$	—	3	—	μs
Turn-off time	t_{OFF}		—	80	—	μs

Switching Time Test Circuit









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